METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is included forming an oxide film on a substrate by alternately performing: forming the first oxide film containing an atom X by performing a first cycle including non-simultaneously performing forming a first layer including a component in which a first functional group is bonded to the atom X, and forming a second layer containing the atom X and oxygen by oxidizing the first layer; and forming the second oxide film containing the atom X by performing a second cycle including non-simultaneously performing forming a third layer including a component in which the first functional group is bonded to the atom X, and forming a fourth layer containing the atom X and oxygen by oxidizing the third layer, under a processing condition that an oxidizing power is higher than an oxidizing power when oxidizing the first layer.

FIG. 4